

40V P-Channel Enhancement Mode MOSFET

Voltage

-40 V

Current

-55 A

Features

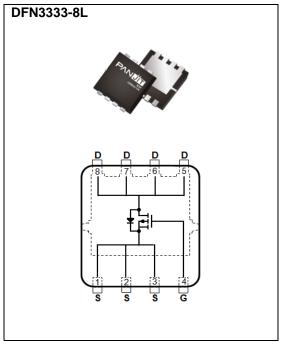
- R_{DS(ON)}, V_{GS}@-10V, I_D@-10A<11.6mΩ
- RDS(ON), VGS@-4.5V, ID@-6A<17.6m Ω
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±25	V
Continuous Drain Current(Note 3)	T _C =25°C		-55	
	Tc=100°C	I _D	-39	A
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-162	
Power Dissipation	T _C =25°C	5	63	14/
	Tc=100°C	Po	31	W
Continuous Drain Current(Note 4)	T _A =25°C		-11	
	T _A =70°C	I _D	-9.2	A
Power Dissipation	T _A =25°C	D-	2.5	14/
	T _A =70°C	Pb —	1.8	W
Single Pulse Avalanche Energy(Note 5)		Eas	110	mJ
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	2.1	°C/W
	Junction to Ambient	R _{θJA}	60	



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static	•						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10A	-	9.3	11.6	0	
		V _{GS} =-4.5V, I _D =-6A -		13.5	17.6	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA	
Dynamic ^(Note 6)	•			•			
Total Gate Charge	Q_g		-	56	-		
Gate-Source Charge	Qgs	V _{DS} =-32V, I _D =-10A,	-	8.4	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	18	-		
Input Capacitance	Ciss)/ OF)/)/ O)/	-	2858	-	pF	
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V,	-	228	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	179	-		
Gate resistance	Rg	f=1MHz	-	2.9	-	Ω	
Turn-On Delay Time	td _(on)	\/ 00\/ L 40A	-	11	-		
Turn-On Rise Time	tr	V _{DS} =-32V, I _D =-10A,	-	10	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=-10V$, $R_{G}=3\Omega$	-	47	-	ns	
Turn-Off Fall Time	tf	(Note 2)	-	24	-		
Drain-Source Diode							
Diode Forward Current	Is	Tc=25°C	-	-	-55	А	
Pulsed Diode Forward Current	I _{SM}	1c=25 C	-	-	-162		
Diode Forward Voltage	V _{SD}	Is=-20A, V _{GS} =0V	-	-0.85	-1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =-20A	-	29	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	24	-	nC	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=-21A, V_{DD}=-30V, V_{GS}=-10V, Starting T_J=25°C.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

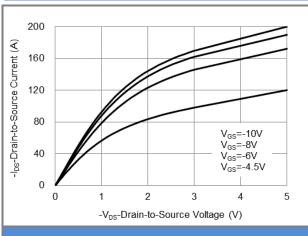


Fig.1 On-Region Characteristics

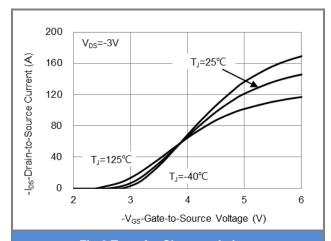


Fig.2 Transfer Characteristics

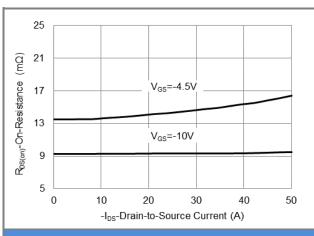


Fig.3 On-Resistance vs. Drain Current

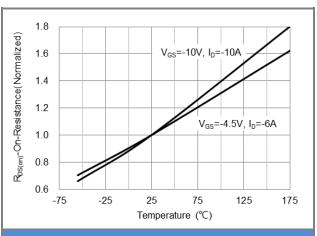
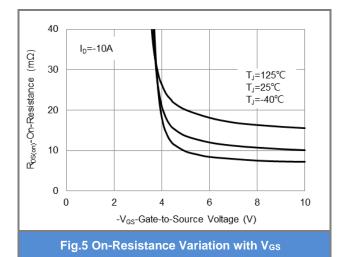


Fig.4 On-Resistance vs. Junction temperature



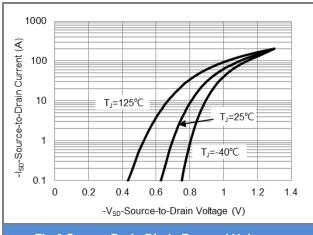


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

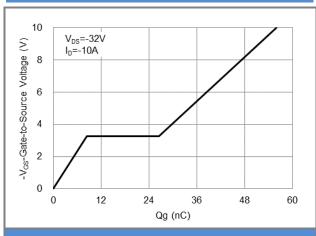


Fig.7 Gate-Charge Characteristics

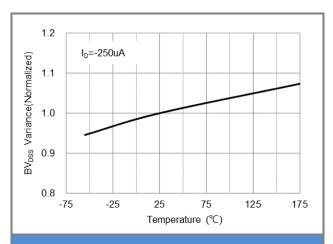


Fig.8 Breakdown Voltage Variation vs. Temperature

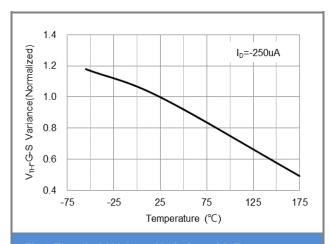


Fig.9 Threshold Voltage Variation with Temperature

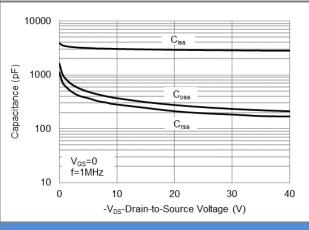
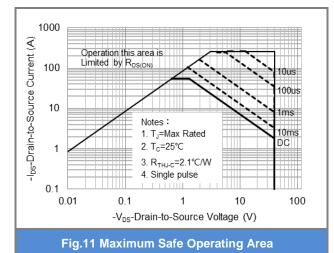
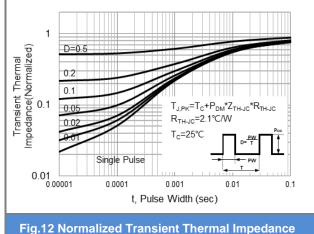


Fig.10 Capacitance vs. Drain-Source Voltage





PJQ4453EP-AU-REV.01 December 26,2024 Page 4



TYPICAL CHARACTERISTIC CURVES

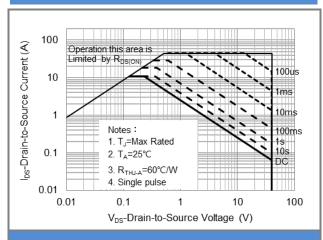


Fig.13 Maximum Safe Operating Area

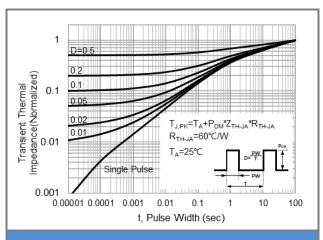


Fig.14 Normalized Transient Thermal Impedance

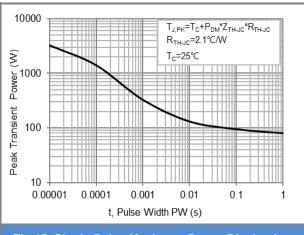


Fig.15 Single Pulse Maximum Power Dissipation

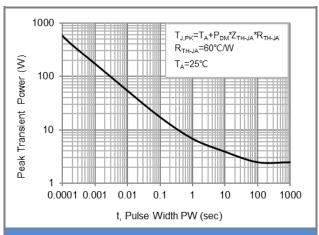


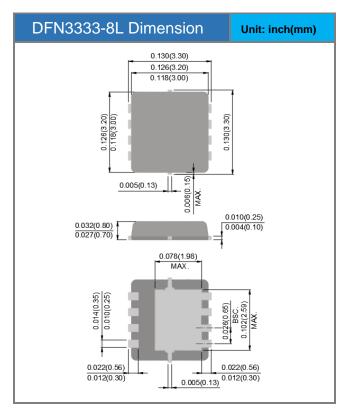
Fig.16 Single Pulse Maximum Power Dissipation

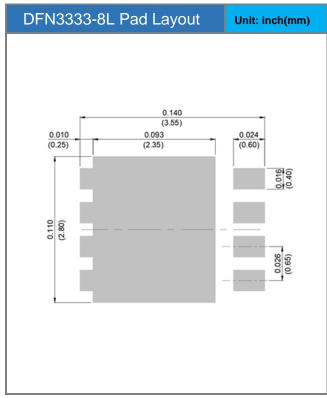


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4453EP-AU	DFN3333-8L	5K pcs / 13" reel	453E	

Packaging Information & Mounting Pad Layout







Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
 responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
 representation or warranty that such applications will be suitable for the specified use without further testing or
 modification.
- The products shown herein are not designed and authorized for equipments relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.